



PTO/SB/08B (10-01)

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Substitute for form 1449B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>			Complete if Known		
			Application Number	Not Yet Assigned	
			Filing Date	April 16, 2004	
			First Named Inventor	Kristy A. Campbell, et al.	
			Group Art Unit	Not Yet Assigned	
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Sheet	1	of	9	Attorney Docket Number	M4065.0703/P703-A

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No.†	Document Number Number-Kind Code* (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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Substitute for form 1449B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Complete if Known	
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